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## (54) IMPROVED POSITIVE TYPE PHOTORESIST DEVELOPING SOLUTION

## (57)Abstract:

PURPOSE: To prevent residues of a thin film and scum at the exposed areas after development by incorporating an alkali contg. no metal ion, a quaternary ammonium salt type cationic surfactant, and a monovalent alcohol in a developing soln.

CONSTITUTION: The developing soln. capable of enhancing the solubility of a resist film at the exposed areas and preventing the residues of the thin resist film and the scum contains the alkali contg. no metal ion., such as amines, heterocyclic bases, or quaternary ammonium bases; the quaternary ammonium type cationic surfactant for enhancing selective solubility between the exposed and nonexposed areas, optimally, such as trimethyl-coconut oil derived alkyl- ammonium chloride; and as the third component to be added to a combination of said two, a kind of alcohol, embodied by methanol or ethanol.

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